

DISCRETE SEMICONDUCTORS

Microwave transistors

RF & MICROWAVE

SEMICONDUCTORS & MODULES

RADAR PULSED POWER TRANSISTORS

type number	f (GHz)	V _{CC} (V)	t _p (μs)	δ (%)	P _L ²⁾ (W)	G _p ²⁾ (dB)	η _c ²⁾ (%)	envelope
L-band								
RZ1214B35Y	1.2 to 1.4	50	150	5	35	7	30	FO57C
RZ1214B35Y	1.2 to 1.4	50	300	10	40. ¹⁾	7. ¹⁾	35. ¹⁾	FO57C
RZ1214B65Y	1.2 to 1.4	50	150	5	70	7	35	FO57C
RZ1214B65Y	1.2 to 1.4	50	300	10	80. ¹⁾	7. ¹⁾	30. ¹⁾	FO57C
RX1214B130Y	1.2 to 1.4	50	150	5	130	7	35	FO91
RX1214B150W	1.2 to 1.4	50	1000	10	135	6.5	35	FO91
RX1214B150W	1.2 to 1.4	50	150	5	220. ¹⁾	8. ¹⁾	45. ¹⁾	FO91
RX1214B170W	1.2 to 1.4	42	500	10	170	6.7	40	FO91
RX1214B300Y	1.2 to 1.4	50	150	5	250	7	35	FO91
RX1214B300Y	1.2 to 1.4	50	300	10	300. ¹⁾	7.5 ¹⁾	35. ¹⁾	FO91
RX1214B350Y	1.2 to 1.4	50	130	6	280	7	40	FO91
S-band								
RN2731B110W	2.7 to 3.1	40	100	10	110	7.5	40	TBF
RN3034B80W	3 to 3.4	40	100	10	80	6.5	35	TBF
RO2731B10W	2.7 to 3.1	40	100	10	12.5	7.5	40	TBF
RO2731B20W	2.7 to 3.1	40	100	10	25	7.5	40	TBF
RO2731B50W	2.7 to 3.1	40	100	10	60	7.5	40	TBF

¹⁾ typical values

²⁾ minimum values